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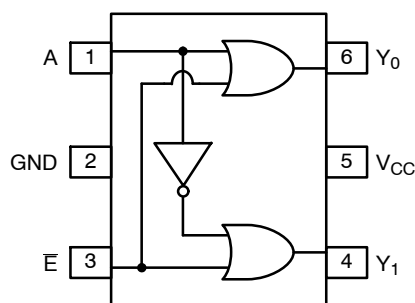
1-to-2 Decoder/ Demultiplexer

NL7SZ19

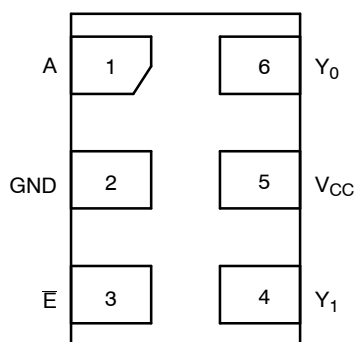
The NL7SZ19 is a 1-to-2 decoder. When the output enable (\bar{E}) is Low, the device passes data at input A to outputs Y0 (true) and Y1 (complement). The NL7SZ19 can also be used as a 1-to-2 demultiplexer. As a demultiplexer, data at input E is routed to either Y0 or Y1 depending on the state of A. The device operates over the voltage range from 1.65 V to 5.5 V.

Features

- Designed for 1.65 V to 5.5 V V_{CC} Operation
- 2.7 ns t_{PD} at $V_{CC} = 5$ V (Typ)
- Inputs/Outputs Overvoltage Tolerant up to 5.5 V
- I_{OFF} Supports Partial Power Down Protection
- Sink 32 mA at 5.0 V
- Available in SC-88, SC-74 and UDFN6 Packages
- Chip Complexity < 100 FETs
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



SC-88 / SC-74



UDFN6

Figure 1. Pinout (Top View)



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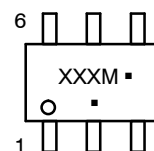
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MARKING DIAGRAMS

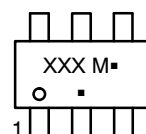


1

SC-88
DF SUFFIX
CASE 419B



SC-74
CASE 318F-05



1

UDFN6, 1.2x1.0, 0.4P
CASE 517AA-01



X, XXX = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 6 of this data sheet.

NL7SZ19

PIN ASSIGNMENT

Pin	Function
1	A
2	GND
3	\bar{E}
4	Y_1
5	V_{CC}
6	Y_0

FUNCTION TABLE

\bar{E}	A	$Y_0 = A + \bar{E}$	$Y_1 = \bar{A} + \bar{E}$
L	L	L	H
L	H	H	L
H	H	H	H
H	L	H	H

MAXIMUM RATINGS

Symbol	Characteristics	Value	Unit	
V_{CC}	DC Supply Voltage NLV	-0.5 to +7.0 -0.5 to +6.5	V	
V_{IN}	DC Input Voltage NLV	-0.5 to +7.0 -0.5 to +6.5	V	
V_{OUT}	DC Output Voltage (NLV) Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode ($V_{CC} = 0$ V)	-0.5 to $V_{CC} + 0.5$ -0.5 to +7.0 -0.5 to +7.0	V	
V_{OUT}	DC Output Voltage Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode ($V_{CC} = 0$ V)	-0.5 to $V_{CC} + 0.5$ -0.5 to +6.5 -0.5 to +6.5	V	
I_{IK}	DC Input Diode Current $V_{IN} < GND$	-50	mA	
I_{OK}	DC Output Diode Current $V_{OUT} < GND$	-50	mA	
I_{OUT}	DC Output Source/Sink Current	± 50	mA	
I_{CC} or I_{GND}	DC Supply Current per Supply Pin or Ground Pin	± 100	mA	
T_{STG}	Storage Temperature Range	-65 to +150	$^{\circ}C$	
T_L	Lead Temperature, 1 mm from Case for 10 secs	260	$^{\circ}C$	
T_J	Junction Temperature Under Bias	+150	$^{\circ}C$	
θ_{JA}	Thermal Resistance (Note 2)	SC-88 SC-74 UDFN6	377 320 154	$^{\circ}C/W$
P_D	Power Dissipation in Still Air	SC-88 SC-74 UDFN6	332 390 812	mW
MSL	Moisture Sensitivity	Level 1	-	
F_R	Flammability Rating Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	-	
V_{ESD}	ESD Withstand Voltage (Note 3) Human Body Model Charged Device Model	2000 1000	V	
$I_{Latchup}$	Latchup Performance (Note 4)	± 100	mA	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Applicable to devices with outputs that may be tri-stated.
2. Measured with minimum pad spacing on an FR4 board, using 10mm-by-1inch, 2 ounce copper trace no air flow per JESD51-7.
3. HBM tested to ANSI/ESDA/JEDEC JS-001-2017. CDM tested to EIA/JESD22-C101-F. JEDEC recommends that ESD qualification to EIA/JESD22-A115-A (Machine Model) be discontinued per JEDEC/JEP172A.
4. Tested to EIA/JESD78 Class II.

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RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics	Min	Max	Unit
V_{CC}	Positive DC Supply Voltage	1.65	5.5	V
V_{IN}	DC Input Voltage	0	5.5	V
V_{OUT}	DC Output Voltage	0	V_{CC}	V
	Active-Mode (High or Low State)	0	5.5	
	Tri-State Mode (Note 1) Power-Down Mode ($V_{CC} = 0$ V)	0	5.5	
T_A	Operating Temperature Range	-55	+125	°C
t_r, t_f	Input Rise and Fall Time			ns
	$V_{CC} = 1.65$ V to 1.95 V	0	20	
	$V_{CC} = 2.3$ V to 2.7 V	0	20	
	$V_{CC} = 3.0$ V to 3.6 V	0	10	
	$V_{CC} = 4.5$ V to 5.5 V	0	5	

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Condition	V_{CC} (V)	$T_A = 25^\circ\text{C}$			$-55^\circ\text{C} \leq T_A \leq 125^\circ\text{C}$		Units
				Min	Typ	Max	Min	Max	
V_{IH}	High-Level Input Voltage		1.65 to 1.95	$0.65 V_{CC}$	-	-	$0.65 V_{CC}$	-	V
			2.3 to 5.5	$0.70 V_{CC}$	-	-	$0.70 V_{CC}$	-	
V_{IL}	Low-Level Input Voltage		1.65 to 1.95	-	-	$0.35 V_{CC}$	-	$0.35 V_{CC}$	V
			2.3 to 5.5	-	-	$0.30 V_{CC}$	-	$0.30 V_{CC}$	
V_{OH}	High-Level Output Voltage	$V_{IN} = V_{IH}$ or V_{IL} $I_{OH} = -100 \mu\text{A}$ $I_{OH} = -4 \text{ mA}$ $I_{OH} = -8 \text{ mA}$ $I_{OH} = -16 \text{ mA}$ $I_{OH} = -24 \text{ mA}$ $I_{OH} = -32 \text{ mA}$	1.65 to 5.5	$V_{CC} - 0.1$	V_{CC}	-	$V_{CC} - 0.1$	-	V
			1.65	1.29	1.52	-	1.29	-	
			2.3	1.9	2.1	-	1.9	-	
			3	2.4	2.7	-	2.4	-	
			3	2.3	2.5	-	2.3	-	
			4.5	3.8	4	-	3.8	-	
V_{OL}	Low-Level Output Voltage	$V_{IN} = V_{IH}$ or V_{IL} $I_{OH} = 100 \mu\text{A}$ $I_{OH} = 4 \text{ mA}$ $I_{OH} = 8 \text{ mA}$ $I_{OH} = 16 \text{ mA}$ $I_{OH} = 24 \text{ mA}$ $I_{OH} = 32 \text{ mA}$	1.65 to 5.5	-	-	0.1	-	0.1	V
			1.65	-	0.08	0.24	-	0.24	
			2.3	-	0.12	0.3	-	0.3	
			3	-	0.24	0.4	-	0.4	
			3	-	0.26	0.55	-	0.55	
			4.5	-	0.31	0.55	-	0.55	
I_{IN}	Input Leakage Current	$V_{IN} = 5.5$ V or GND	1.65 to 5.5	-	-	± 0.1	-	± 1.0	μA
I_{OFF}	Power Off Leakage Current	$V_{IN} = 5.5$ V or $V_{OUT} = 5.5$ V	0	-	-	1.0	-	10	μA
I_{CC}	Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5	-	-	1.0	-	10	μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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AC ELECTRICAL CHARACTERISTICS

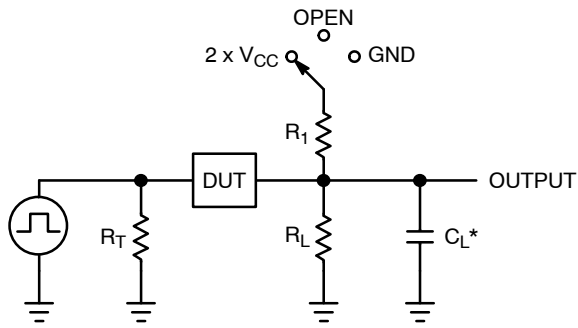
Symbol	Parameter	Condition	V _{CC} (V)	T _A = 25°C			-55°C ≤ T _A ≤ 125°C		Units
				Min	Typ	Max	Min	Max	
t _{PLH} , t _{PHL}	Propagation Delay, A to Y (Figures 2 and 3)	R _L = 1 MΩ, C _L = 15 pF	1.65 to 1.95	-	6.2	10.5	-	11.0	ns
		R _L = 1 MΩ, C _L = 15 pF	2.3 to 2.7	-	3.6	6.0	-	6.4	
		R _L = 1 MΩ, C _L = 15 pF	3.0 to 3.6	-	2.9	4.1	-	4.5	
				-	3.2	5.1	-	5.4	
		R _L = 1 MΩ, C _L = 15 pF	4.5 to 5.5	-	2.4	3.2	-	3.5	
		R _L = 500 Ω, C _L = 50 pF		-	2.7	4.0	-	4.3	

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Units
C _{IN}	Input Capacitance	V _{CC} = 5.5 V, V _{IN} = 0 V or V _{CC}	2.5	pF
C _{OUT}	Output Capacitance	V _{CC} = 5.5 V, V _{IN} = 0 V or V _{CC}	2.5	pF
C _{PD}	Power Dissipation Capacitance (Note 10)	10 MHz, V _{CC} = 3.3 V, V _{IN} = 0 V or V _{CC}	9	pF
		10 MHz, V _{CC} = 5.5 V, V _{IN} = 0 V or V _{CC}	11	

5. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

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C_L includes probe and jig capacitance
 R_T is Z_{OUT} of pulse generator (typically 50 Ω)
 $f = 1$ MHz

Figure 2. Test Circuit

Test	Switch Position	C_L , pF	R_L , Ω	R_1 , Ω
t_{PLH} / t_{PHL}	Open	See AC Characteristics Table		
t_{PLZ} / t_{PZL}	$2 \times V_{CC}$	50	500	500
t_{PHZ} / t_{PZH}	GND	50	500	500

X = Don't Care



Figure 3. Switching Waveforms

V_{CC} , V	V_{mi} , V	V_{mo} , V		V_Y , V
		t_{PLH} , t_{PHL}	t_{PZL} , t_{PLZ} , t_{PZH} , t_{PHZ}	
1.65 to 1.95	$V_{CC}/2$	$V_{CC}/2$	$V_{CC}/2$	0.15
2.3 to 2.7	$V_{CC}/2$	$V_{CC}/2$	$V_{CC}/2$	0.15
3.0 to 3.6	$V_{CC}/2$	$V_{CC}/2$	$V_{CC}/2$	0.3
4.5 to 5.5	$V_{CC}/2$	$V_{CC}/2$	$V_{CC}/2$	0.3

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DEVICE ORDERING INFORMATION

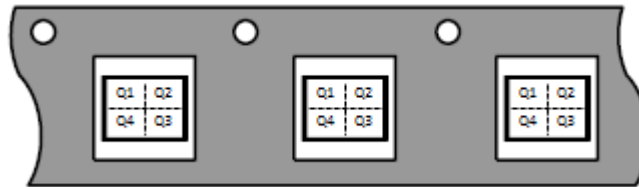
Device	Packages	Specific Device Code	Pin 1 Orientation (See below)	Shipping†
NL7SZ19DFT2G	SC-88	LE	Q4	3000 / Tape & Reel
NLV7SZ19DFT2G*	SC-88	LE	Q4	3000 / Tape & Reel
NL7SZ19DBVT1G	SC-74	AK	Q4	3000 / Tape & Reel
NL7SZ19MU2TCG (In Development)	UDFN6, 1.2 x 1.0, 0.4P	U	Q2	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

Pin 1 Orientation in Tape and Reel

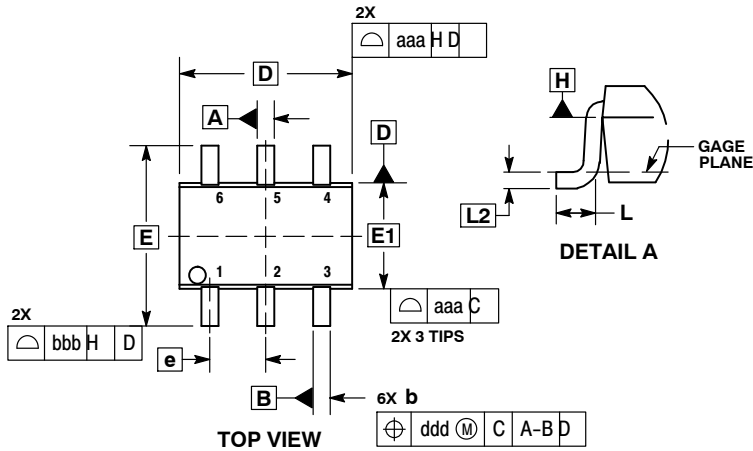
Direction of Feed



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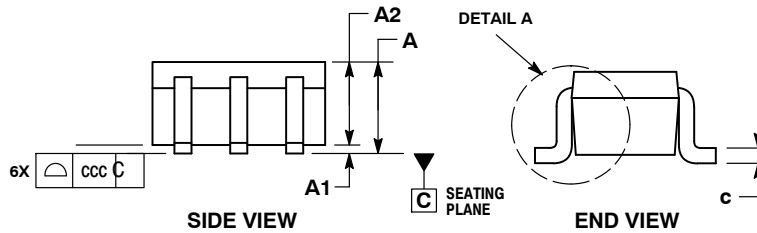
PACKAGE DIMENSIONS

SC – 88/SC70 – 6/SOT – 363
 CASE 419B – 02
 ISSUE Y

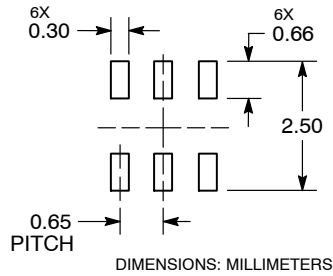


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
 4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
 5. DATUMS A AND B ARE DETERMINED AT DATUM H.
 6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
 7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	--	--	-1.10	--	--	-0.043
A1	0.00	--	0.10	0.000	--	0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.010
C	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.070	0.078	0.086
E	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.26	0.36	0.46	0.010	0.014	0.018
L2	0.15 BSC			0.006 BSC		
aaa	0.15			0.006		
bbb	0.30			0.012		
ccc	0.10			0.004		
ddd	0.10			0.004		



RECOMMENDED SOLDERING FOOTPRINT*

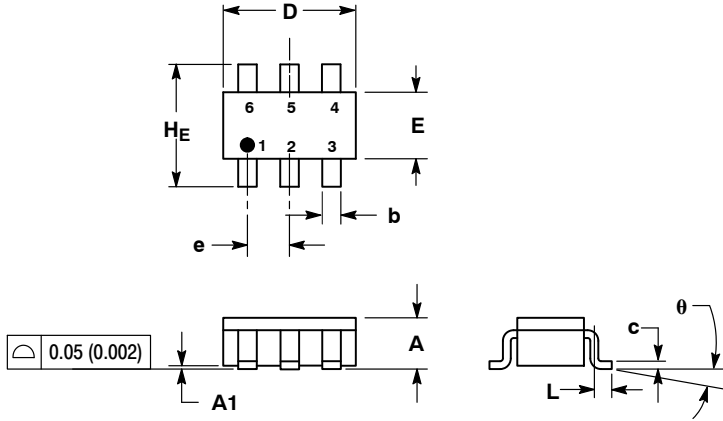


*For additional information on our Pb – Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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PACKAGE DIMENSIONS

SC-74
CASE 318F-05
ISSUE N

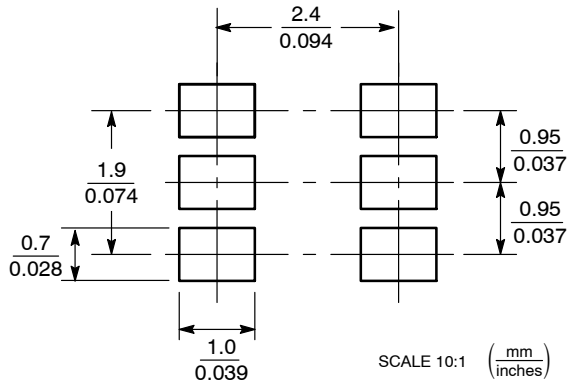


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318F-01, -02, -03, -04 OBSOLETE. NEW STANDARD 318F-05.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.90	1.00	1.10	0.035	0.039	0.043
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.25	0.37	0.50	0.010	0.015	0.020
c	0.10	0.18	0.26	0.004	0.007	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	0.85	0.95	1.05	0.034	0.037	0.041
L	0.20	0.40	0.60	0.008	0.016	0.024
HE	2.50	2.75	3.00	0.099	0.108	0.118
θ	0°	-	10°	0°	-	10°

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.